



Supporting Information

Temperature-Dependent Structural and Electrical Properties of Metal-Organic CVD MoS₂ Films

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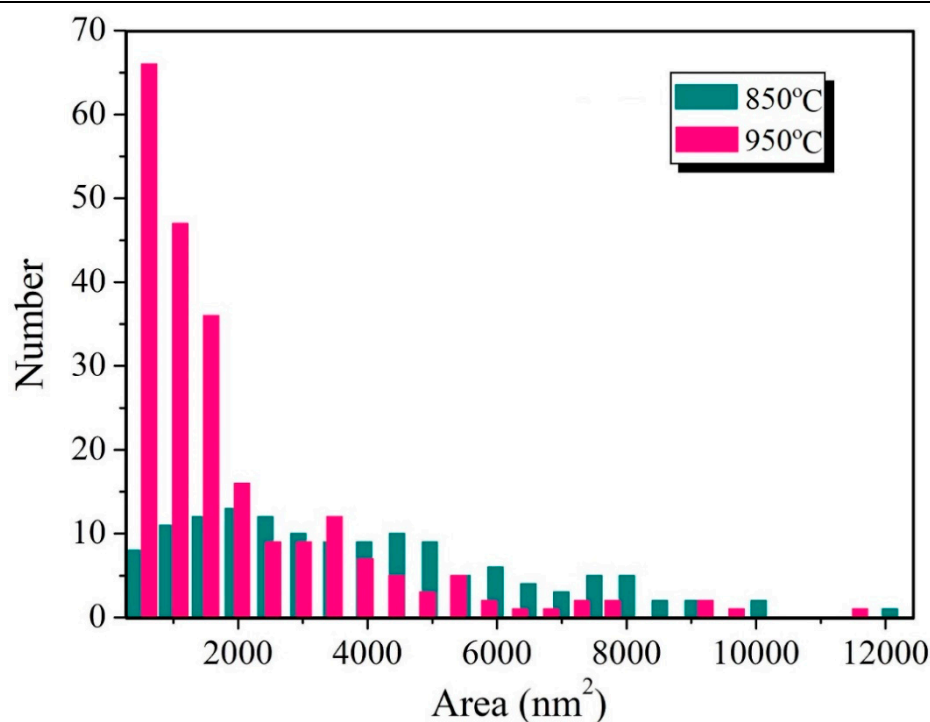


Figure S1. Crystallite size distribution histogram for MoS₂ samples deposited at 850 °C and 950 °C.

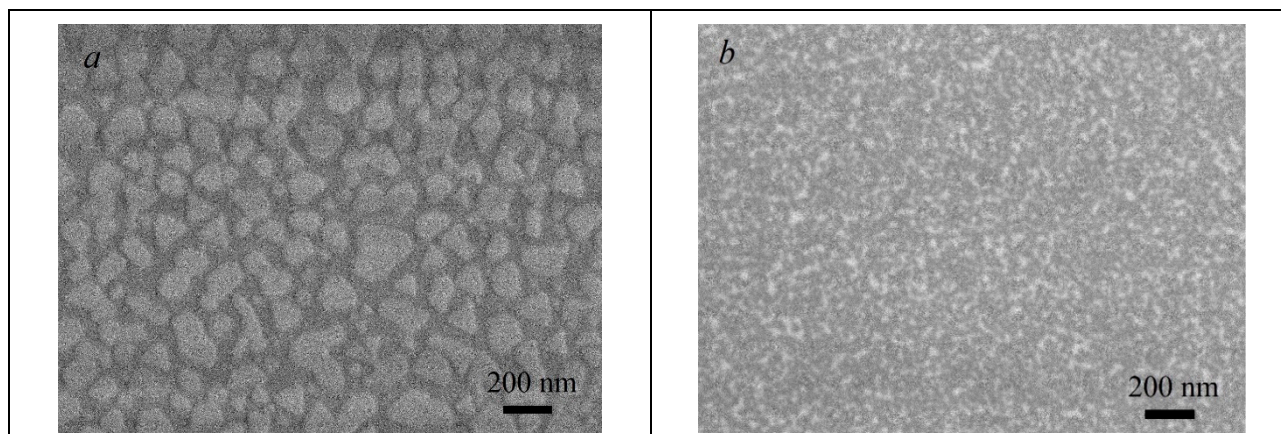


Figure S2- SEM-images of MoS₂ films' surface, deposited at 950 °C for 9 hours (a) and at 650 °C for 6 hours (b). The brighter regions correspond to thicker film grains, darker background to the thinner underlying film.

